

## P-Channel 30 V (D-S) MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
- 30	0.068 at V <sub>GS</sub> = - 10 V	- 4.6	4.6
	0.110 at V <sub>GS</sub> = - 4.5 V	- 3.4	

SCHOTTKY PRODUCT SUMMARY		
V <sub>KA</sub> (V)	V <sub>F</sub> (V) Diode Forward Voltage	I <sub>D</sub> (A) <sup>a</sup>
30	0.44 V at 1 A	2

### FEATURES

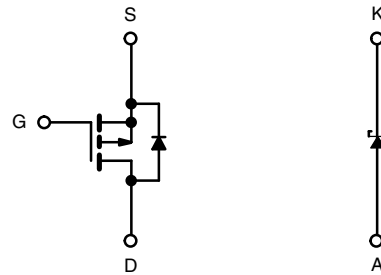
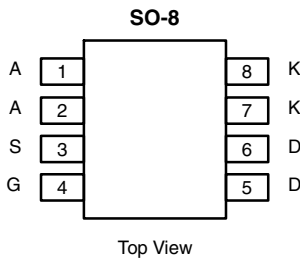
- Halogen-free According to IEC 61249-2-21 Definition
- LITTLE FOOT<sup>®</sup> Plus Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Battery Management in Notebook PC
- Non-synchronous Buck Converter in HDD



Ordering Information: Si4833BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage (MOSFET)	V <sub>DS</sub>	- 30	V	
Reverse Voltage (Schottky)	V <sub>KA</sub>	- 30		
Gate-Source Voltage (MOSFET)	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) (MOSFET)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 4.6	
		T <sub>C</sub> = 70 °C	- 3.6	
		T <sub>A</sub> = 25 °C	- 3.8 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	- 3 <sup>b, c</sup>	
Pulsed Drain Current (MOSFET) (t = 300 μs)	I <sub>DM</sub>	- 20	A	
Continuous Source Current (MOSFET Diode Conduction)	I <sub>S</sub>	T <sub>C</sub> = 25 °C		- 2
		T <sub>A</sub> = 25 °C		- 1.4 <sup>b, c</sup>
Average Forward Current (Schottky)	I <sub>F</sub>	- 1.4 <sup>b</sup>		W
Pulsed Forward Current (Schottky)	I <sub>FM</sub>	- 2		
Maximum Power Dissipation (MOSFET and Schottky)	P <sub>D</sub>	T <sub>C</sub> = 25 °C	2.75	
		T <sub>C</sub> = 70 °C	1.75	
		T <sub>A</sub> = 25 °C	1.75 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	1.10 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET and Schottky) <sup>b, c, d</sup>	R <sub>thJA</sub>	60	71.5	°C/W
Maximum Junction-to-Foot (Drain) (MOSFET and Schottky)	R <sub>thJF</sub>	35	45	

Notes:

- Based on T<sub>C</sub> = 25 °C.
- Surface mounted on FR4 board.
- t ≤ 10 s.
- Maximum under steady state conditions is 120 °C/W.

<b>MOSFET SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-20		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			3.9		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1	-1.8	-2.5	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 75\text{ }^\circ\text{C}$			-10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq -5\text{ V}, V_{GS} = -10\text{ V}$	-5			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3.6\text{ A}$		0.055	0.068	$\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -2.8\text{ A}$		0.092	0.110	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -3.6\text{ A}$		6.5		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		350		pF
Output Capacitance	$C_{oss}$			75		
Reverse Transfer Capacitance	$C_{rss}$			63		
Total Gate Charge	$Q_g$	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -5\text{ A}$		9	14	nC
				4.6	7	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		1.3		
Gate-Drain Charge	$Q_{gd}$			2.1		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	1.5	7.3	14.5	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		28	50	ns
Rise Time	$t_r$			73	140	
Turn-Off Delay Time	$t_{d(off)}$			12	24	
Fall Time	$t_f$			8	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 3\text{ }\Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		6	12	
Rise Time	$t_r$			9	18	
Turn-Off Delay Time	$t_{d(off)}$			12	24	
Fall Time	$t_f$			6	12	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			-4.6	A
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				-20	
Body Diode Voltage	$V_{SD}$	$I_S = -2\text{ A}, V_{GS} = 0\text{ V}$		-0.83	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		12	24	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			6	12	nC
Reverse Recovery Fall Time	$t_a$			8		ns
Reverse Recovery Rise Time	$t_b$			4		

Notes:

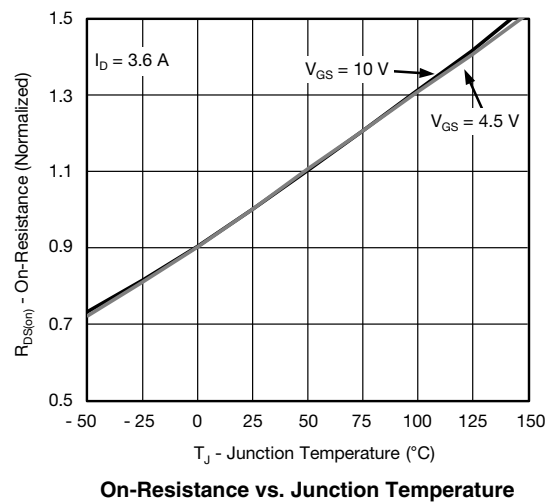
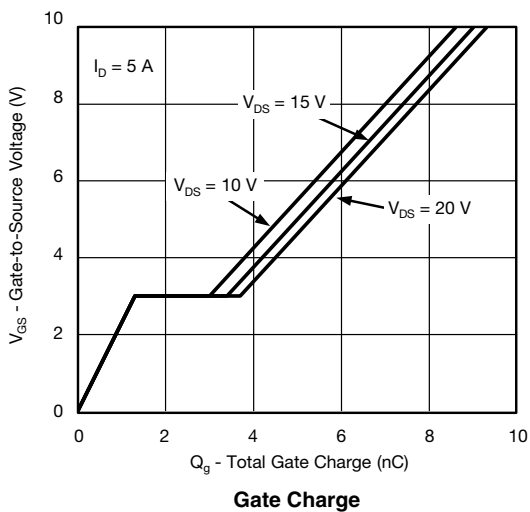
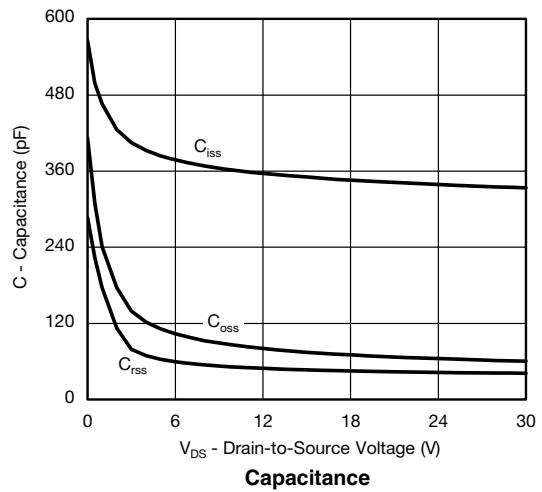
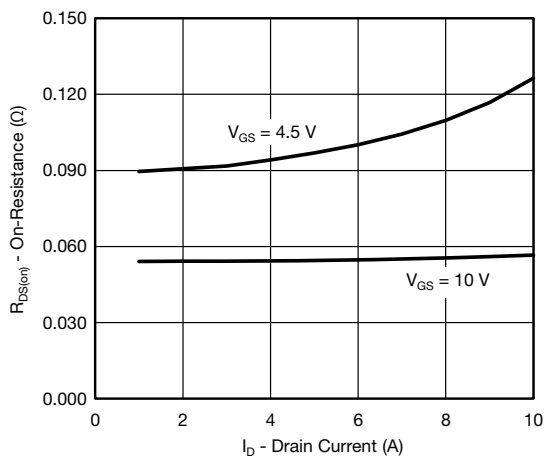
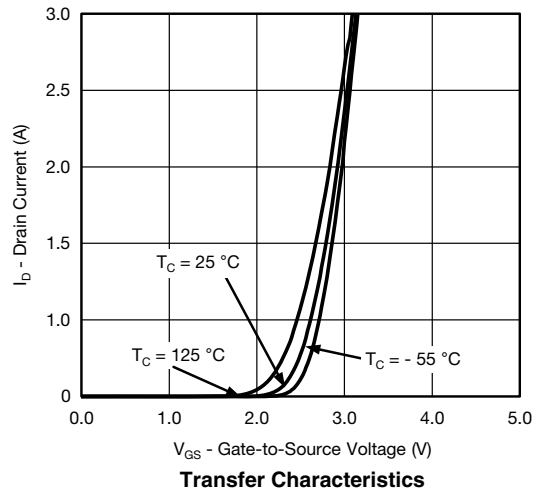
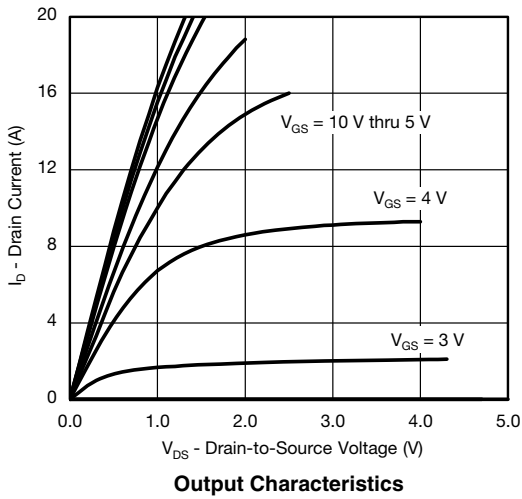
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.



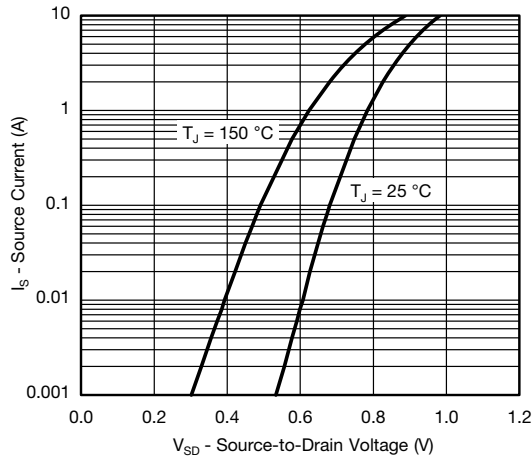
<b>SCHOTTKY SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	$V_F$	$I_F = 1\text{ A}$		0.36	0.44	V
		$I_F = 1\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.29	0.35	
Maximum Reverse Leakage Current	$I_{rm}$	$V_R = 30\text{ V}$		0.03	0.2	mA
		$V_R = 30\text{ V}, T_J = 75\text{ }^\circ\text{C}$		0.6	5	
		$V_R = 30\text{ V}, T_J = 125\text{ }^\circ\text{C}$		7.5	60	
Junction Capacitance	$C_T$	$V_R = 15\text{ V}$		5.3		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

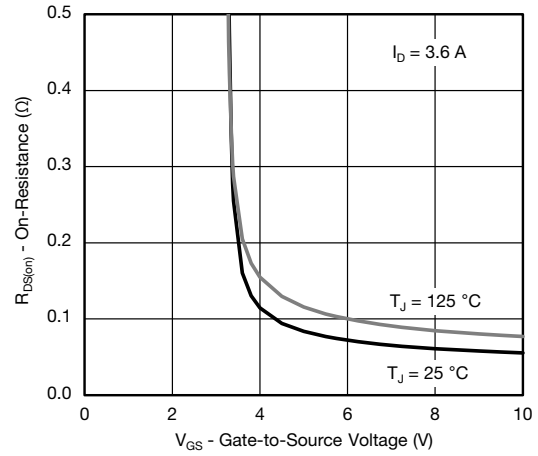
## MOSFET TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



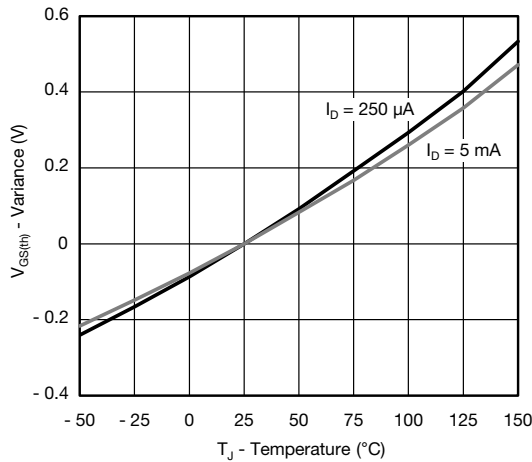
**MOSFET TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



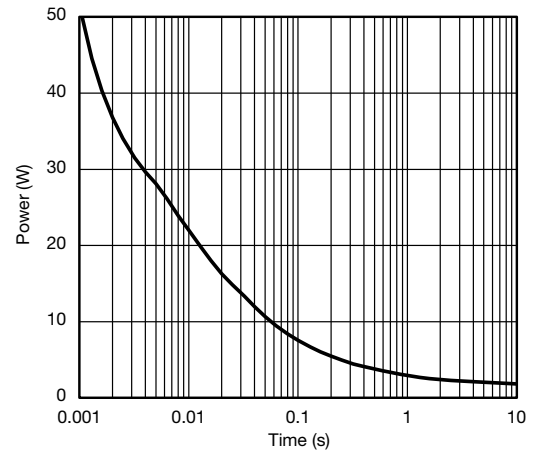
**Source-Drain Diode Forward Voltage**



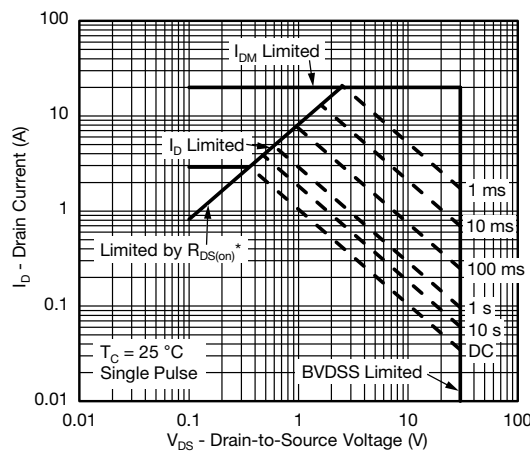
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**

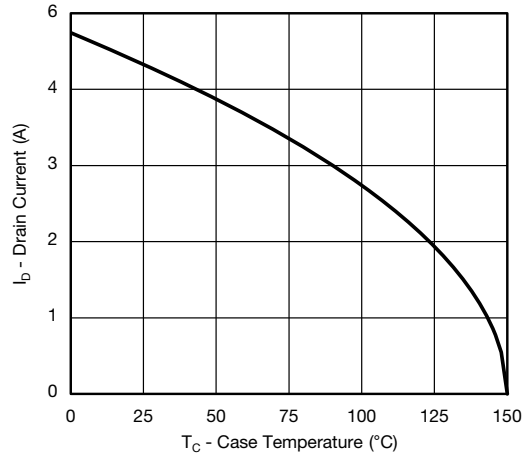


**Single Pulse Power, Junction-to-Ambient**

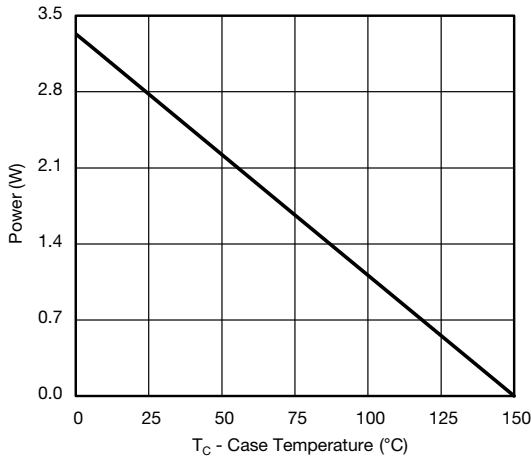


**Safe Operating Area, Junction-to-Case**

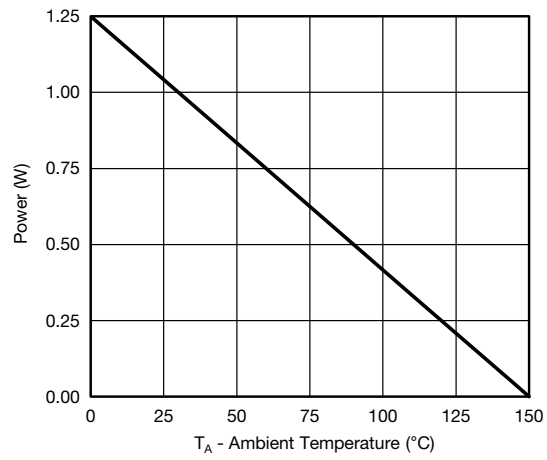
**MOSFET TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating\***



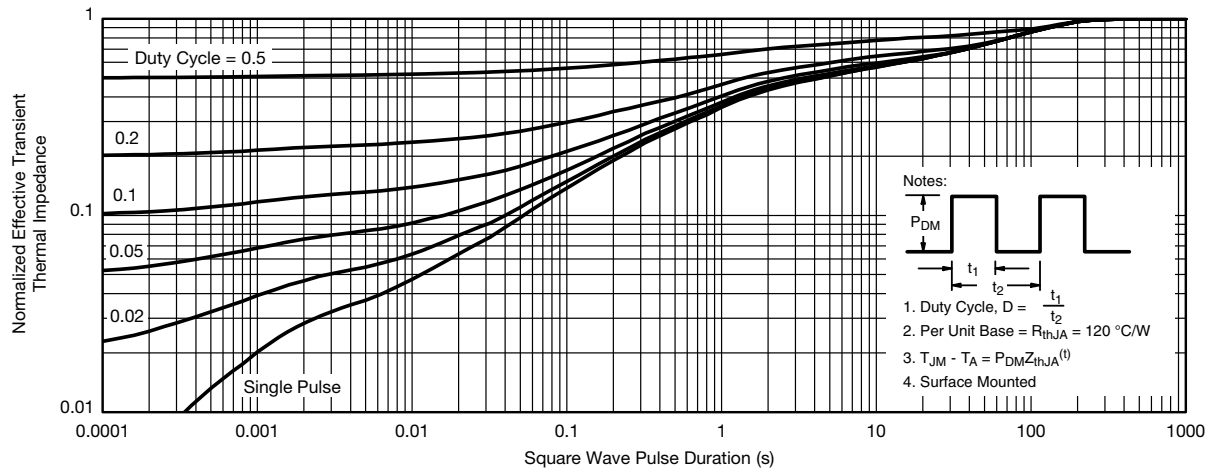
**Power Derating, Junction-to-Foot**



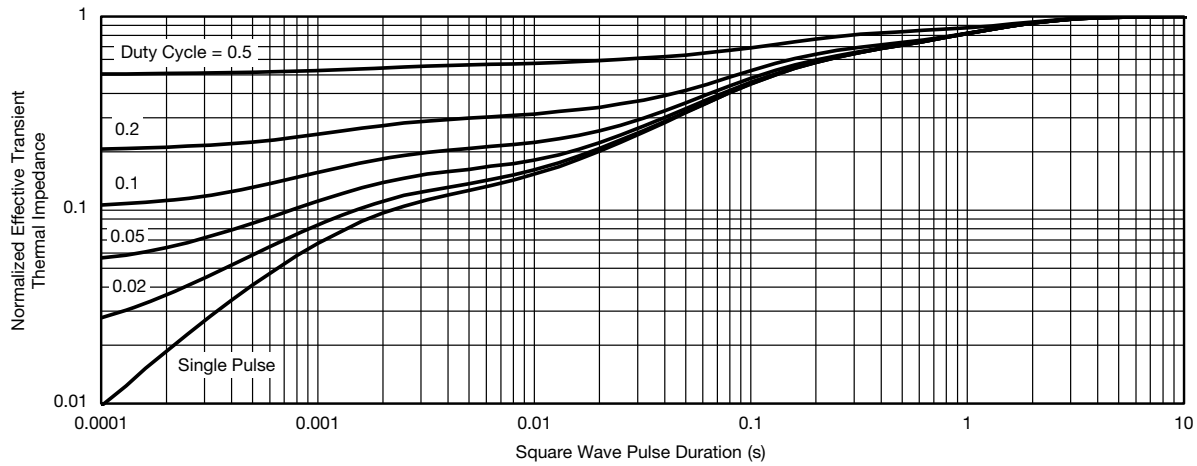
**Power Derating, Junction-to-Ambient**

\* The power dissipation P<sub>D</sub> is based on T<sub>J(max)</sub> = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**MOSFETS TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

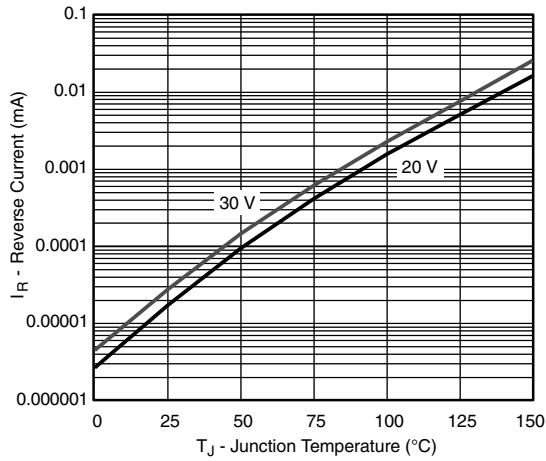


**Normalized Thermal Transient Impedance, Junction-to-Ambient**

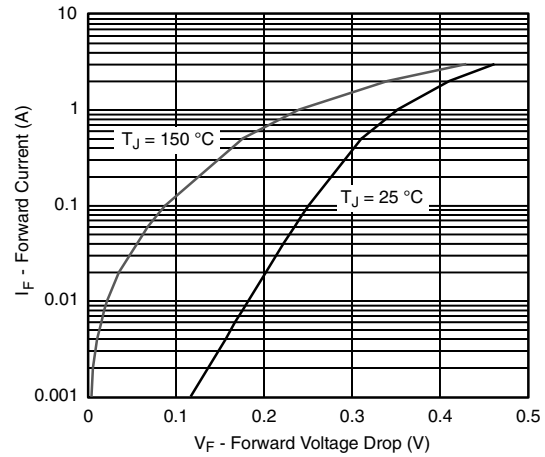


**Normalized Thermal Transient Impedance, Junction-to-Foot**

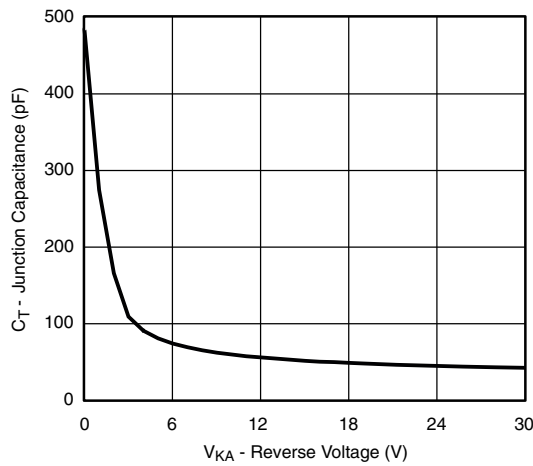
## SCHOTTKY TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Reverse Current vs. Junction Temperature



Forward Voltage Drop



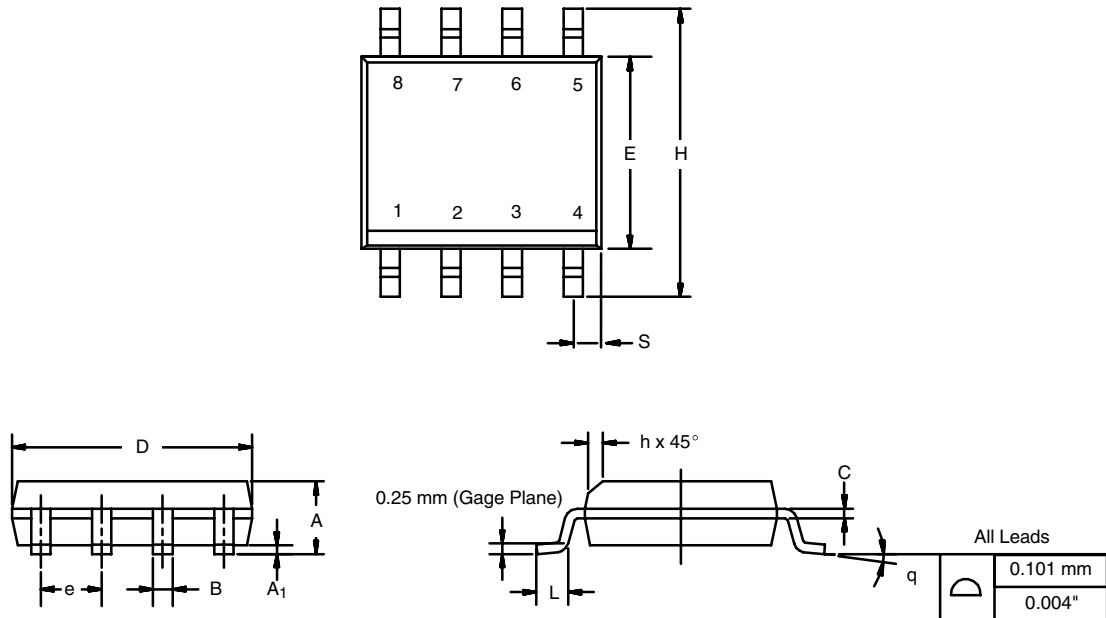
Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?67537](http://www.vishay.com/ppg?67537).



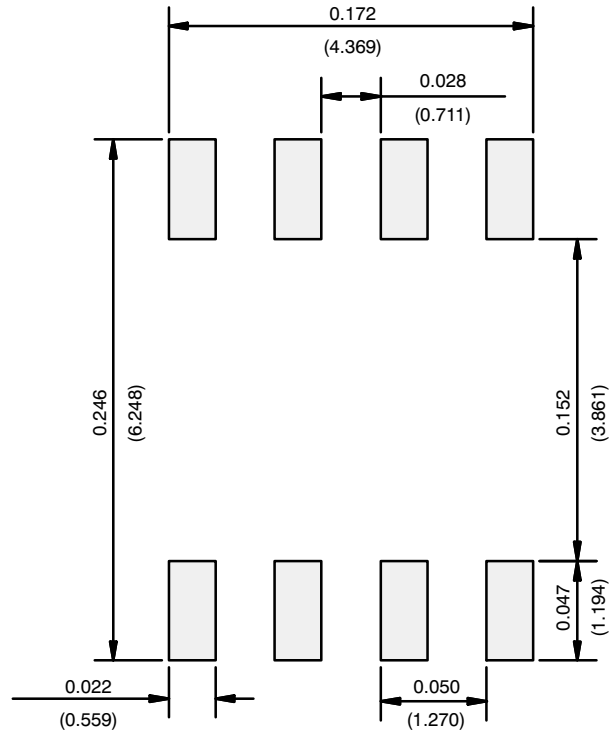
## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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